

ABSTRACT

NEGATIVE PHOTORESIST COMPOSITION FOR KRF LASER FOR FORMING SEMICONDUCTOR PATTERNS

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Disclosed is a negative photoresist composition for a KrF laser for semiconductor pattern formation, which includes a predetermined compound in order to improve the properties of a conventional negative photoresist, thereby realizing
10 high transparency, high resolution and an excellent profile, even in the presence of an exposure source having a short wavelength compared to the conventional negative photoresist, and is thus suitable for use in semiconductor processing.